

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	5847823	(substrate base stem superstrate super adj strate wafer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/30 15:49
L2	1921011	insulat\$4 dielectric	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/30 15:35
L3	4964624	film layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/30 15:35
L4	1081	(metal m) near4 (silicon si) near4 (o oxygen) near4 (n nitrogen nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/30 15:39
L5	47350	(nitride nitrogen n) near2 bond\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/30 15:39
L6	5283905	gate electrode contact	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/30 15:40
L7	25	4 with 5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/30 15:40

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L8	263234	1.clm.	US-PGPUB	OR	ON	2006/01/30 15:49
L9	78309	2.clm.	US-PGPUB	OR	ON	2006/01/30 15:51
L10	192571	3.clm.	US-PGPUB	OR	ON	2006/01/30 15:51
L11	69	4.clm.	US-PGPUB	OR	ON	2006/01/30 15:52
L12	2376	5.clm.	US-PGPUB	OR	ON	2006/01/30 15:52
L13	204343	6.clm.	US-PGPUB	OR	ON	2006/01/30 15:53
L14	64	8 and 9 and 10 and 12 and 13	US-PGPUB	OR	ON	2006/01/30 15:54
L15	4	14 and 11	US-PGPUB	OR	ON	2006/01/30 15:54